Supporting Information

Facile rearrangement of molecular layer deposited metalcone thin film by electron beam irradiation for area selective atomic layer deposition

Seunghwan Lee,‡a GeonHo Baek,‡b Hye-mi Kim,a Yong-Hwan Kimc and Jin-Seong Park*ab

a Division of Materials Science and Engineering, Hanyang University, 222 Wangsimni-ro, Seongdong-gu, Seoul 04763, Republic of Korea

b Division of Nano-Scale Semiconductor Engineering, Hanyang University, 222 Wangsimni-ro, Seongdong-gu, Seoul 04763, Republic of Korea

c Infovion Inc., 71 Gyeongin-ro, Yeoungdeungpo-gu, Seoul 07286, Republic of Korea

†These authors contributed equally to this work. (Seunghwan Lee (sevenfoku@hanyang.ac.kr)
and GeonHo Baek (qorrjsgh00@hanyang.ac.kr)

*Corresponding Author: jsparklime@hanyang.ac.kr
Figure S1. AFM roughness of indicone (HQ) and alucone (4MP) films grown on a Si wafer.
Figure S2. Shift of G band position in (a) indicone (HQ), and (b) alucone (4MP). (c) Intensity ratio of D and G peak in indicone (HQ) and alucone (4MP)